

TLE2062, TLE2062A, TLE2062B, TLE2062Y EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE μ POWER DUAL OPERATIONAL AMPLIFIERS

SLOS044E – OCTOBER 1989 – REVISED AUGUST 1994

- **Excellent Output Drive Capability**
 $V_O = \pm 2.5 \text{ V Min at } R_L = 100 \ \Omega$,
 $V_{CC\pm} = \pm 5 \text{ V}$
 $V_O = \pm 12.5 \text{ V Min at } R_L = 600 \ \Omega$,
 $V_{CC\pm} = \pm 15 \text{ V}$
- **Low Supply Current**
 $280 \ \mu\text{A Typ Per Amplifier}$
- **High Unity-Gain Bandwidth . . . 2 MHz Typ**
- **High Slew Rate . . . 3.4 V/ $\mu\text{s Typ}$**
- **Macromodels Included**
- **Wide Operating Supply Voltage Range**
 $V_{CC\pm} = \pm 3.5 \text{ V to } \pm 19 \text{ V}$
- **High Open-Loop Gain . . . 230 V/mV Typ**
- **Low Offset Voltage . . . 1 mV Max**
- **Low Offset Voltage Drift With Time**
 $0.04 \ \mu\text{V/mo Typ}$
- **Low Input Bias Current . . . 4 pA Typ**

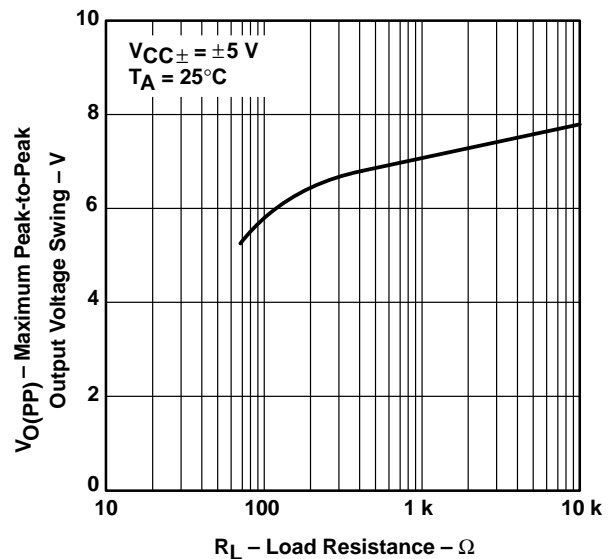
description

The TLE2062, TLE2062A, TLE2062B, and TLE2062Y are JFET-input, low power, precision dual operational amplifiers manufactured using Texas Instruments Excalibur process. These devices combine outstanding output drive capability with low power consumption, excellent dc precision, and wide bandwidth.

In addition to maintaining the traditional JFET advantages of fast slew rates and low input bias and offset currents, the Excalibur process offers outstanding parametric stability over time and temperature. This results in a precision device remaining precise even with changes in temperature and over years of use.

The TLE2062, TLE2062A, and TLE2062B are ideal choices for any application requiring excellent dc precision, high output drive, wide bandwidth, and low power consumption.

**MAXIMUM PEAK-TO-PEAK
OUTPUT VOLTAGE SWING
vs
LOAD RESISTANCE**



AVAILABLE OPTIONS

PACKAGED DEVICES						CHIP FORM (Y)
T_A	V_{IOmax} AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	
0°C to 70°C	1 mV 2 mV 4 mV	TLE2062BCD TLE2062ACD TLE2062CD	— — —	— — —	TLE2062BCP TLE2062ACP TLE2062CP	— — TLE2062Y
-40°C to 85°C	1 mV 2 mV 4 mV	TLE2062BID TLE2062AID TLE2062ID	— — —	— — —	TLE2062BIP TLE2062AIP TLE2062IP	— — —
-55°C to 125°C	1 mV 2 mV 4 mV	TLE2062BMD TLE2062AMD TLE2062MD	TLE2062BMFK TLE2062AMFK TLE2062MFK	TLE2062BMJG TLE2062AMJG TLE2062BMJG	TLE2062BMP TLE2062AMP TLE2062BMP	— — —

The D packages are available taped and reeled. Add R suffix to device type (e.g., TLE2062ACDR). Chips are tested at 25 °C.

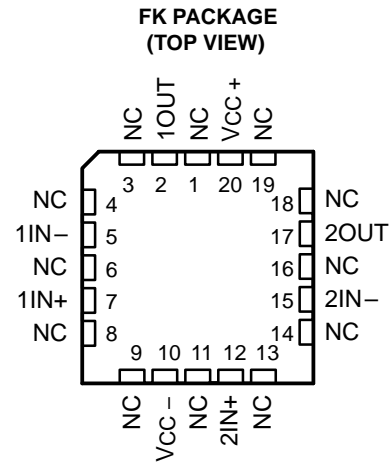
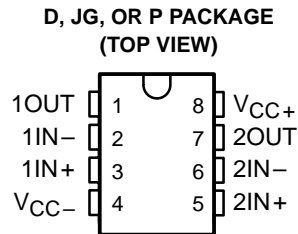
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description (continued)

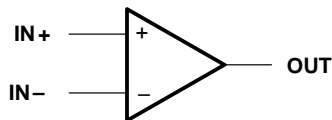
A variety of available package options includes small-outline and chip-carrier versions for high-density system applications.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from –40°C to 85°C. The M-suffix devices are characterized for operation over the full military temperature range of –55°C to 125°C.

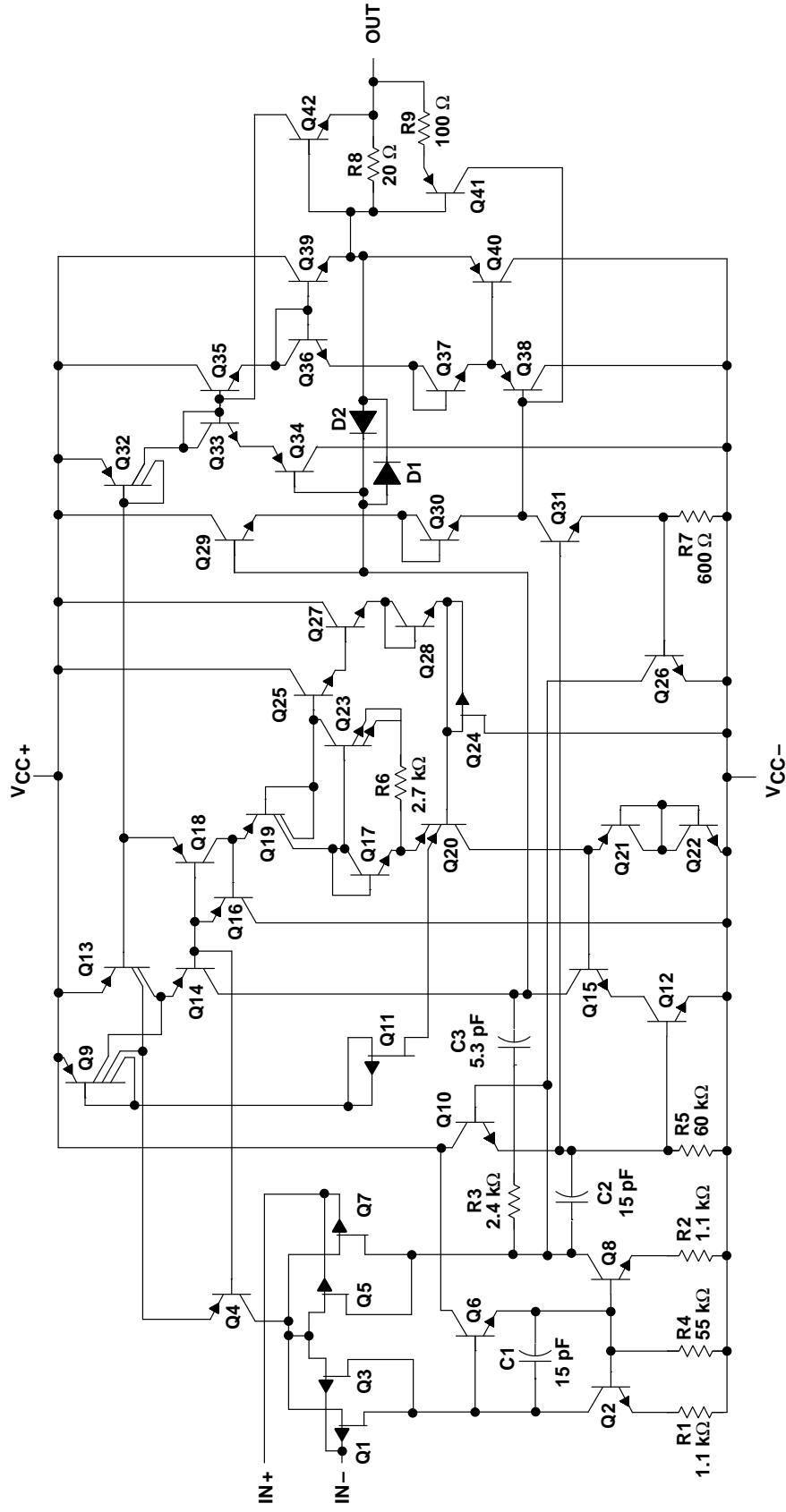


NC – No internal connection

symbol



equivalent schematic (each channel)



ACTUAL DEVICE COMPONENT COUNT	
Transistors	42
Resistors	9
Diodes	2
Capacitors	3

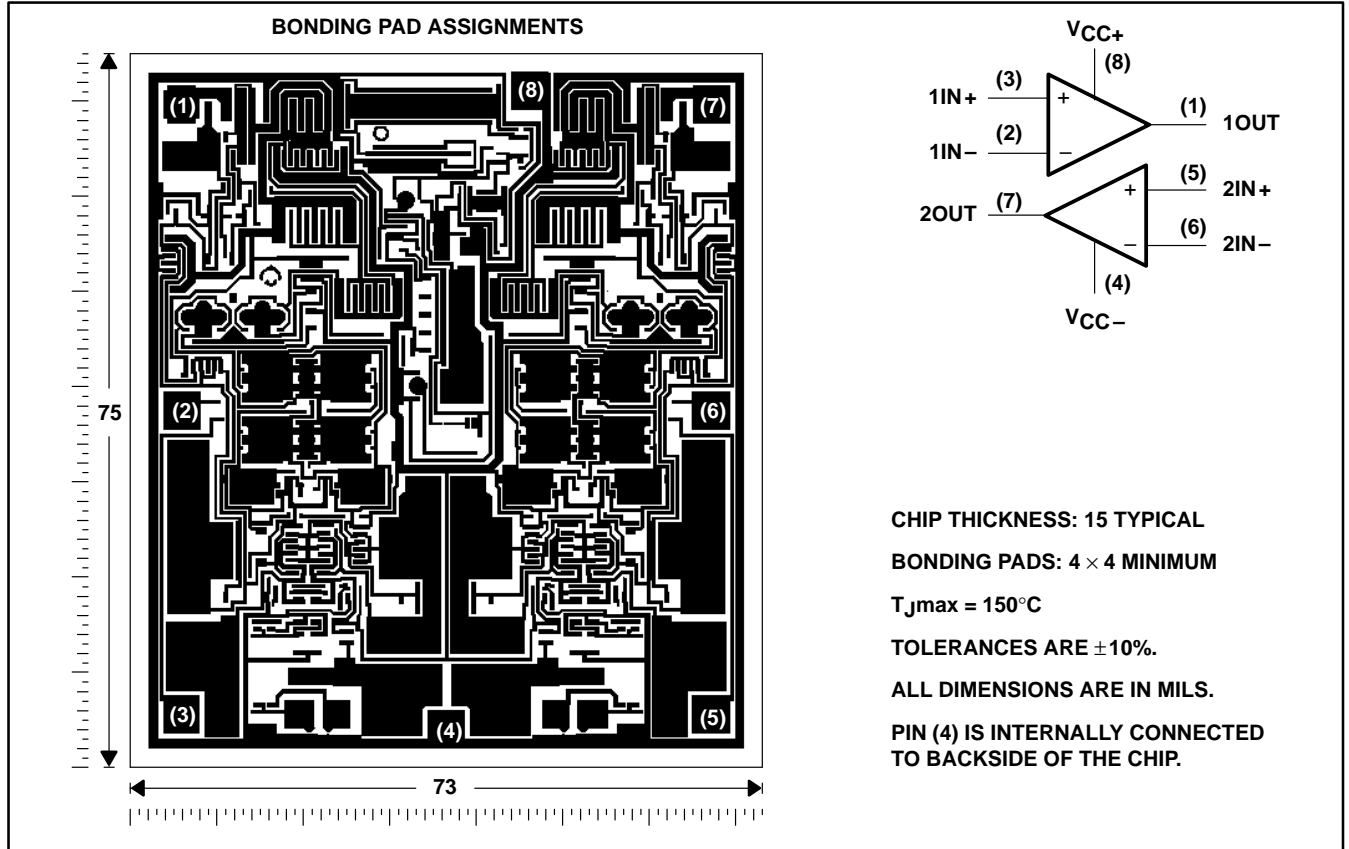
Component values are nominal.

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TLE2062Y chip information

This chip, when properly assembled, displays characteristics similar to the TLE2062. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{CC+} (see Note 1)	19 V
Supply voltage, V_{CC-}	-19 V
Differential input voltage, V_{ID} (see Note 2)	±38 V
Input voltage, V_I (any input)	± V_{CC}
Input current, I_I (each input)	±1 mA
Output current, I_O (each output)	±80 mA
Total current into V_{CC+}	80 mA
Total current out of V_{CC-}	80 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	unlimited
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A : C suffix	0°C to 70°C
I suffix	-40°C to 85°C
M suffix	-55°C to 125°C
Storage temperature range	-65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D or P package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG package	300°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-} .
 2. Differential voltages are at $IN+$ with respect to $IN-$.
 3. The output may be shorted to either supply. Temperatures and/or supply voltages must be limited to ensure that the maximum dissipation rate is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	145 mW
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
P	1000 mW	8.0 mW/°C	640 mW	520 mW	200 mW

recommended operating conditions

		C SUFFIX		I SUFFIX		M SUFFIX		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Supply voltage, $V_{CC\pm}$		±3.5	±18	±3.5	±18	±3.5	±18	V
Common-mode input voltage, V_{IC}	$V_{CC\pm} = \pm 5\text{ V}$	-1.6	4	-1.6	4	-1.6	4	V
	$V_{CC\pm} = \pm 15\text{ V}$	-11	13	-11	13	-11	13	
Operating free-air temperature, T_A		0	70	-40	85	-55	125	°C



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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A †	TLE2062C TLE2062AC TLE2062BC			UNIT
				MIN	TYP	MAX	
V_{IO} Input offset voltage	TLE2062C	$V_{IC} = 0, R_S = 50 \Omega$	25°C	1	5	mV	
			Full range	5.9			
	TLE2062AC		25°C	0.9	4		
			Full range	4.9			
	TLE2062BC		25°C	0.7	3		
			Full range	3.9			
α_{VIO} Temperature coefficient of input offset voltage		Full range	6		$\mu V/^\circ C$		
Input offset voltage long-term drift (see Note 4)			25°C	0.04		$\mu V/mo$	
I_{IO} Input offset current			25°C	1	pA		
			Full range	0.8		nA	
I_{IB} Input bias current			25°C	3		pA	
			Full range	2		nA	
V_{ICR} Common-mode input voltage range			25°C	-1.6 to 4	-2 to 6	V	
			Full range	-1.6 to 4		V	
V_{OM+} Maximum positive peak output voltage swing	$R_L = 10 k\Omega$		25°C	3.5	3.7	V	
		Full range	3.3				
	$R_L = 100 \Omega$	25°C	2.5	3.1			
		Full range	2				
V_{OM-} Maximum negative peak output voltage swing	$R_L = 10 k\Omega$		25°C	-3.7	-3.9	V	
		Full range	-3.3				
	$R_L = 100 \Omega$	25°C	-2.5	-2.7			
		Full range	-2				
A_{VD} Large-signal differential voltage amplification	$V_O = \pm 2.8$ V, $R_L = 10 k\Omega$		25°C	15	80	V/mV	
		Full range	2				
	$V_O = 0$ to 2 V, $R_L = 100 \Omega$	25°C	0.75	45			
		Full range	0.5				
	$V_O = 0$ to -2 V, $R_L = 100 \Omega$	25°C	0.5	3			
		Full range	0.25				
r_i Input resistance		25°C	10^{12}		Ω		
c_i Input capacitance		25°C	4		pF		
z_o Open-loop output impedance	$I_O = 0$	25°C	560		Ω		
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}, R_S = 50 \Omega$	25°C	65	82	dB		
		Full range	65				
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5$ V to ± 15 V, $R_S = 50 \Omega$	25°C	75	93	dB		
		Full range	75				

† Full range is 0°C to 70°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	T_A †	TLE2062C TLE2062AC TLE2062BC			UNIT
			MIN	TYP	MAX	
I_{CC} Supply current	$V_O = 0$, No load	25°C		560	620	μA
		Full range			635	
ΔI_{CC} Supply-current change over operating temperature range		Full range		26		μA

† Full range is 0°C to 70°C.

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5\text{ V}$

PARAMETER	TEST CONDITIONS	T_A †	TLE2062C TLE2062AC TLE2062BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C	2.2	3.4		V/μs
		Full range	2.1			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10\text{ Hz}$, $R_S = 20\ \Omega$	25°C		59	100	nV/√Hz
	$f = 1\text{ kHz}$, $R_S = 20\ \Omega$	25°C		43	60	
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }10\text{ Hz}$	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1\text{ kHz}$	25°C		1		fA/√Hz
THD Total harmonic distortion	$V_{O(PP)} = 2\text{ V}$, $R_L = 10\text{ k}\Omega$, $A_{VD} = 2$, $f = 10\text{ kHz}$	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		1.8		MHz
	$R_L = 100\ \Omega$, $C_L = 100\text{ pF}$	25°C		1.3		
Settling time	0.1%	25°C		5		μs
	0.01%	25°C		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10\text{ k}\Omega$	25°C		140		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		58°		
	$R_L = 100\ \Omega$, $C_L = 100\text{ pF}$	25°C		75°		

† Full range is 0°C to 70°C.

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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A †	TLE2062C TLE2062AC TLE2062BC			UNIT
				MIN	TYP	MAX	
V_{IO} Input offset voltage	TLE2062C	$V_{IC} = 0, R_S = 50 \Omega$	25°C	0.9	4	mV	
			Full range		4.9		
			25°C	0.8	2		
	TLE2062AC		Full range		2.9		
			25°C	0.5	1		
			Full range		1.9		
	TLE2062BC		Full range		6		$\mu V/^\circ C$
			25°C	0.04			$\mu V/mo$
			25°C	2			pA
I_{IO} Input offset current			25°C	2		pA	
I_{IB} Input bias current			Full range		1	nA	
			25°C	4		pA	
I_{IB} Input bias current			Full range		3	nA	
			25°C	-11 to 13	-12 to 16	V	
V_{ICR} Common-mode input voltage range			Full range	-11 to 13		V	
			25°C	13.2	13.7	V	
V_{OM+} Maximum positive peak output voltage swing	$R_L = 10 k\Omega$	Full range		13			
		25°C	12.5	13.2			
V_{OM-} Maximum negative peak output voltage swing	$R_L = 600 \Omega$	Full range		12			
		25°C	-13.2	-13.7			
	$R_L = 10 k\Omega$	Full range		-13			
		25°C	-12.5	-13			
A_{VD} Large-signal differential voltage amplification	$V_O = \pm 10 \psi, R_L = 10 k\Omega$	25°C	30	230	V/mV		
		Full range		20			
	$V_O = 0 \text{ to } 8 \text{ V}, R_L = 600 \Omega$	25°C	25	100			
		Full range		10			
$V_O = 0 \text{ to } -8 \text{ V}, R_L = 600 \Omega$	25°C	3	25				
	Full range		1				
r_i Input resistance			25°C	10^{12}		Ω	
c_i Input capacitance			25°C	4		pF	
z_o Open-loop output impedance	$I_O = 0$		25°C	560	Ω		
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}, R_S = 50 \Omega$	25°C	72	90	dB		
		Full range		70			
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5 \text{ V to } \pm 15 \text{ V}, R_S = 50 \Omega$	25°C	75	93	dB		
		Full range		75			

† Full range is 0°C to 70°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)
(continued)

PARAMETER	TEST CONDITIONS	T_A †	TLE2062C TLE2062AC TLE2062BC			UNIT
			MIN	TYP	MAX	
I_{CC} Supply current	$V_O = 0$ V, No load	25°C	625	690	μA	
		Full range	715			
ΔI_{CC} Supply-current change over operating temperature range		Full range	36		μA	

† Full range is 0°C to 70°C.

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V

PARAMETER	TEST CONDITIONS	T_A †	TLE2062C TLE2062AC TLE2062BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C	2.6	3.4	V/μs	
		Full range	2.5			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10$ Hz, $R_S = 20$ Ω	25°C	70	100	nV/√Hz	
	$f = 1$ kHz, $R_S = 20$ Ω	25°C	40	60		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1$ Hz to 10 Hz	25°C	1.1		μV	
I_n Equivalent input noise current	$f = 1$ kHz	25°C	1.1		fA/√Hz	
THD Total harmonic distortion	$V_{O(PP)} = 2$ V, $R_L = 10$ kΩ, $A_{VD} = 2$, $f = 10$ kHz	25°C	0.025%			
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C	2		MHz	
	$R_L = 600$ Ω, $C_L = 100$ pF	25°C	1.5			
Settling time	0.1%	25°C	5		μs	
	0.01%	25°C	10			
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10$ kΩ	25°C	40		kHz	
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C	60°			
	$R_L = 600$ Ω, $C_L = 100$ pF	25°C	70°			

† Full range is 0°C to 70°C.

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PARAMETER		TEST CONDITIONS	T_A †	TLE2062I TLE2062AI TLE2062BI			UNIT
				MIN	TYP	MAX	
V_{IO}	Input offset voltage	$V_{IC} = 0, R_S = 50 \Omega$	25°C	1	5	mV	
			Full range	6.3			
			25°C	0.9	4		
			Full range	5.3			
			25°C	0.7	3		
			Full range	4.3			
α_{VIO}	Temperature coefficient of input offset voltage	$V_{IC} = 0, R_S = 50 \Omega$	Full range	6		$\mu V/^\circ C$	
	Input offset voltage long-term drift (see Note 4)		25°C	0.04		$\mu V/mo$	
I_{IO}	Input offset current		25°C	1		pA	
			Full range	2		nA	
I_{IB}	Input bias current		25°C	3		pA	
			Full range	4		nA	
V_{ICR}	Common-mode input voltage range		25°C	-1.6 to 4	-2 to 6	V	
			Full range	-1.6 to 4		V	
V_{OM+}	Maximum positive peak output voltage swing	$R_L = 10 k\Omega$	25°C	3.5	3.7	V	
			Full range	3.1			
		$R_L = 100 \Omega$	25°C	2.5	3.1		
			Full range	2			
V_{OM-}	Maximum negative peak output voltage swing	$R_L = 10 k\Omega$	25°C	-3.7	-3.9	V	
			Full range	-3.1			
		$R_L = 100 \Omega$	25°C	-2.5	-2.7		
			Full range	-2			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 2.8$ V, $R_L = 10 k\Omega$	25°C	15	80	V/mV	
			Full range	2			
		$V_O = 0$ to 2 V, $R_L = 100 \Omega$	25°C	0.75	45		
			Full range	0.5			
		$V_O = 0$ to -2 V, $R_L = 100 \Omega$	25°C	0.5	3		
			Full range	0.25			
r_i	Input resistance		25°C	10^{12}		Ω	
c_i	Input capacitance		25°C	4		pF	
z_o	Open-loop output impedance	$I_O = 0$	25°C	560		Ω	
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICRmin}, R_S = 50 \Omega$	25°C	65	82	dB	
			Full range	65			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5$ V to ± 15 V, $R_S = 50 \Omega$	25°C	75	93	dB	
			Full range	65			

† Full range is $-40^\circ C$ to $85^\circ C$.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V (unless otherwise noted)
(continued)

PARAMETER	TEST CONDITIONS	T_A †	TLE2062I TLE2062AI TLE2062BI			UNIT
			MIN	TYP	MAX	
I_{CC} Supply current	$V_O = 0$, No load	25°C		560	620	μA
		Full range			640	
ΔI_{CC} Supply-current change over operating temperature range		Full range		54		μA

† Full range is –40°C to 85°C.

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V

PARAMETER	TEST CONDITIONS	T_A †	TLE2062I TLE2062AI TLE2062BI			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C	2.2	3.4		V/μs
		Full range	1.7			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10$ Hz, $R_S = 20$ Ω	25°C		59	100	nV/√Hz
	$f = 1$ kHz, $R_S = 20$ Ω	25°C		43	60	
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1$ Hz to 10 Hz	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1$ kHz	25°C		1		fA/√Hz
THD Total harmonic distortion	$V_{O(PP)} = 2$ V, $R_L = 10$ kΩ, $A_{VD} = 2$, $f = 10$ kHz	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C		1.8		MHz
	$R_L = 100$ Ω, $C_L = 100$ pF	25°C		1.3		
Settling time	0.1%	25°C		5		μs
	0.01%	25°C		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10$ kΩ	25°C		140		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C		58°		
	$R_L = 100$ Ω, $C_L = 100$ pF	25°C		75°		

† Full range is –40°C to 85°C.

TLE2062, TLE2062A, TLE2062B, TLE2062Y
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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A †	TLE2062I TLE2062AI TLE2062BI			UNIT
				MIN	TYP	MAX	
V_{IO}	Input offset voltage	$V_{IC} = 0, R_S = 50 \Omega$	25°C	0.9	4	mV	
			Full range	5.3			
			25°C	0.8	2		
			Full range	3.3			
			25°C	0.5	1		
			Full range	2.3			
α_{VIO}	Temperature coefficient of input offset voltage	$V_{IC} = 0, R_S = 50 \Omega$	Full range	6		$\mu V/^\circ C$	
	Input offset voltage long-term drift (see Note 4)		25°C	0.04		$\mu V/mo$	
I_{IO}	Input offset current		25°C	2		pA	
			Full range	3		nA	
I_{IB}	Input bias current		25°C	4		pA	
			Full range	5		nA	
V_{ICR}	Common-mode input voltage range	25°C	-11 to 13	-12 to 16	V		
		Full range	-11 to 13		V		
V_{OM+}	Maximum positive peak output voltage swing	$R_L = 10 k\Omega$	25°C	13.2	13.7	V	
			Full range	13			
		$R_L = 600 \Omega$	25°C	12.5	13.2		
			Full range	12			
V_{OM-}	Maximum negative peak output voltage swing	$R_L = 10 k\Omega$	25°C	-13.2	-13.7	V	
			Full range	-13			
		$R_L = 600 \Omega$	25°C	-12.5	-13		
			Full range	-12			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10$ V, $R_L = 10 k\Omega$	25°C	30	230	V/mV	
			Full range	20			
		$V_O = 0$ to 8 V, $R_L = 600 \Omega$	25°C	25	100		
			Full range	10			
		$V_O = 0$ to -8 V, $R_L = 600 \Omega$	25°C	3	25		
			Full range	1			
r_i	Input resistance		25°C	10^{12}		Ω	
c_i	Input capacitance		25°C	4		pF	
z_o	Open-loop output impedance	$I_O = 0$	25°C	560		Ω	
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICRmin}, R_S = 50 \Omega$	25°C	72	90	dB	
			Full range	65			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5$ V to ± 15 V, $R_S = 50 \Omega$	25°C	75	93	dB	
			Full range	65			

† Full range is -40°C to 85°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)
(continued)

PARAMETER	TEST CONDITIONS	T_A †	TLE2062I TLE2062AI TLE2062BI			UNIT
			MIN	TYP	MAX	
I_{CC} Supply current	$V_O = 0$, No load	25°C		625	690	μA
		Full range			720	
ΔI_{CC} Supply-current change over operating temperature range		Full range		74		μA

† Full range is –40°C to 85°C.

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V

PARAMETER	TEST CONDITIONS	T_A †	TLE2062I TLE2062AI TLE2062BI			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C	2.6	3.4		V/μs
		Full range	2.1			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10$ Hz, $R_S = 20$ Ω	25°C		70	100	nV/√Hz
	$f = 1$ kHz, $R_S = 20$ Ω	25°C		40	60	
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1$ Hz to 10 Hz	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1$ kHz	25°C		1.1		fA/√Hz
THD Total harmonic distortion	$V_{O(PP)} = 2$ V, $R_L = 10$ kΩ, $A_{VD} = 2$, $f = 10$ kHz	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C		2		MHz
	$R_L = 600$ Ω, $C_L = 100$ pF	25°C		1.5		
Settling time	0.1%	25°C		5		μs
	0.01%	25°C		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10$ kΩ	25°C		40		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C		60°		
	$R_L = 600$ Ω, $C_L = 100$ pF	25°C		70°		

† Full range is –40°C to 85°C.

TLE2062, TLE2062A, TLE2062B, TLE2062Y
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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5\text{ V}$

PARAMETER		TEST CONDITIONS	T_A^\dagger	TLE2062M TLE2062AM TLE2062BM			UNIT
				MIN	TYP	MAX	
V_{IO} Input offset voltage	TLE2062M	$V_{IC} = 0, R_S = 50\ \Omega$	25°C	1		5	mV
			Full range			7	
	TLE2062AM		25°C	0.9		4	
			Full range			6	
	TLE2062BM		25°C	0.7		3	
			Full range			5	
α_{VIO} Temperature coefficient of input offset voltage			Full range	6		$\mu\text{V}/^\circ\text{C}$	
Input offset voltage long-term drift (see Note 4)			25°C	0.04		$\mu\text{V}/\text{mo}$	
I_{IO} Input offset current			25°C	1		pA	
			Full range			15 nA	
I_{IB} Input bias current			25°C	3		pA	
			Full range			30 nA	
V_{ICR} Common-mode input voltage range			25°C	-1.6 to 4	-2 to 6	V	
			Full range	-1.6 to 4		V	
V_{OM+} Maximum positive peak output voltage swing		$R_L = 10\ \text{k}\Omega$	25°C	3.5	3.7	V	
			Full range	3			
	FK and JG packages	$R_L = 600\ \Omega$	25°C	2.5	3.6		
			Full range	2			
	D and P packages	$R_L = 100\ \Omega$	25°C	2.5	3.1		
			Full range	2			
V_{OM-} Maximum negative peak output voltage swing		$R_L = 10\ \text{k}\Omega$	25°C	-3.5	-3.9	V	
			Full range	-3			
	FK and JG packages	$R_L = 600\ \Omega$	25°C	-2.5	-3.5		
			Full range	-2			
	D and P packages	$R_L = 100\ \Omega$	25°C	-2.5	-2.7		
			Full range	-2			
A_{VD} Large-signal differential voltage amplification		$V_O = \pm 2.8\ \text{V}, R_L = 10\ \text{k}\Omega$	25°C	15	80	V/mV	
			Full range	2			
	FK and JG packages	$V_O = 0\ \text{to}\ 2.5\ \text{V}, R_L = 600\ \Omega$	25°C	1	65		
			Full range	0.5			
		$V_O = 0\ \text{to}\ -2.5\ \text{V}, R_L = 600\ \Omega$	25°C	1	16		
			Full range	0.5			
	D and P packages	$V_O = 0\ \text{to}\ 2\ \text{V}, R_L = 100\ \Omega$	25°C	0.75	45		
			Full range	0.5			
		$V_O = 0\ \text{to}\ -2\ \text{V}, R_L = 100\ \Omega$	25°C	0.5	3		
			Full range	0.25			

† Full range is -55°C to 125°C .

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLE2062, TLE2062A, TLE2062B, TLE2062Y
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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_A †	TLE2062M TLE2062AM TLE2062BM			UNIT
			MIN	TYP	MAX	
r_i Input resistance		25°C	10 ¹²			Ω
c_i Input capacitance		25°C	4			pF
z_o Open-loop output impedance	$I_O = 0$	25°C	560			Ω
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}$ $R_S = 50 \Omega$	25°C	65	82		dB
		Full range	60			
kSVR Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5$ V to ± 15 V, $R_S = 50 \Omega$	25°C	75	93		dB
		Full range	65			
I_{CC} Supply current (two amplifiers)	$V_O = 0$, No load	25°C	560	620		μA
		Full range	650			
ΔI_{CC} Supply-current change over operating temperature range (two amplifiers)		Full range	72			μA

† Full range is –55°C to 125°C.

operating characteristics at specified free-air temperature, $T_A = 25^\circ\text{C}$, $V_{CC\pm} = \pm 5$ V

PARAMETER	TEST CONDITIONS	TLE2062M TLE2062AM TLE2062BM			UNIT
		MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	3.4			V/μs
V_n Equivalent input noise voltage (see Figure 2)	$f = 10 \text{ Hz}$, $R_S = 20 \Omega$	59			nV/√Hz
	$f = 1 \text{ kHz}$, $R_S = 20 \Omega$	43			
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$	1.1			μV
I_n Equivalent input noise current	$f = 1 \text{ kHz}$	1			fA/√Hz
THD Total harmonic distortion	$V_{O(PP)} = 2 \text{ V}$, $R_L = 10 \text{ k}\Omega$, $A_{VD} = 2$, $f = 10 \text{ kHz}$	0.025%			
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	1.8			MHz
	$R_L = 600 \Omega$, $C_L = 100 \text{ pF}$	1.3			
Settling time	0.1%	5			μs
	0.01%	10			
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10 \text{ k}\Omega$	140			kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	58°			
	$R_L = 600 \Omega$, $C_L = 100 \text{ pF}$	75°			

† Full range is –55°C to 125°C.



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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A †	TLE2062M TLE2062AM TLE2062BM			UNIT		
				MIN	TYP	MAX			
V_{IO} Input offset voltage	TLE2062M	$V_{IC} = 0, R_S = 50 \Omega$	25°C	0.9	4	mV			
			Full range	6					
	TLE2062AM		25°C	0.8	2				
			Full range	4					
	TLE2062BM		25°C	0.5	1				
			Full range	3					
	α_{VIO} Temperature coefficient of input offset voltage			Full range	6		$\mu V/^\circ C$		
	Input offset voltage long-term drift (see Note 4)			25°C	0.04		$\mu V/mo$		
	I_{IO} Input offset current			25°C	2		pA		
		Full range	20		nA				
I_{IB} Input bias current		25°C	4		pA				
		Full range	40		nA				
V_{ICR} Common-mode input voltage range		25°C	-11 to 13	-12 to 16	V				
		Full range	-11 to 13		V				
V_{OM+} Maximum positive peak output voltage swing	$R_L = 10 k\Omega$	25°C	13	13.7	V				
		Full range	12.5						
	$R_L = 600 \Omega$	25°C	12.5	13.2					
		Full range	11						
V_{OM-} Maximum negative peak output voltage swing	$R_L = 10 k\Omega$	25°C	-13	-13.7	V				
		Full range	-12.5						
	$R_L = 600 \Omega$	25°C	-12.5	-13					
		Full range	-11						
A_{VD} Large-signal differential voltage amplification	$V_O = \pm 10 \psi, R_L = 10 k\Omega$	25°C	30	230	V/mV				
		Full range	20						
	$V_O = 0$ to 8 V, $R_L = 600 \Omega$	25°C	25	100					
		Full range	7						
	$V_O = 0$ to -8 V, $R_L = 600 \Omega$	25°C	3	25					
		Full range	1						
r_i Input resistance		25°C	10^{12}		Ω				
c_i Input capacitance		25°C	4		pF				
z_o Open-loop output impedance	$I_O = 0$	25°C	560		Ω				
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}, R_S = 50 \Omega$	25°C	72	90	dB				
		Full range	65						
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$)	$V_{CC\pm} = \pm 5$ V to ± 15 V, $R_S = 50 \Omega$	25°C	75	93	dB				
		Full range	65						

† Full range is -55°C to 125°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLE2062, TLE2062A, TLE2062B, TLE2062Y
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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_A †	TLE2062M TLE2062AM TLE2062BM			UNIT
			MIN	TYP	MAX	
I_{CC} Supply current	$V_O = 0$, No load	25°C		625	690	μA
		Full range			730	
ΔI_{CC} Supply-current change over operating temperature range		Full range		97		μA

† Full range is –55°C to 125°C.

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V

PARAMETER	TEST CONDITIONS	T_A †	TLE2062M TLE2062AM TLE2062BM			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C	2	3.4		V/μs
		Full range	1.8			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10$ Hz, $R_S = 20$ Ω	25°C		70		nV/√Hz
	$f = 1$ kHz, $R_S = 20$ Ω	25°C		40		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1$ Hz to 10 Hz	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1$ kHz	25°C		1.1		fA/√Hz
THD Total harmonic distortion	$V_{O(PP)} = 2$ V, $R_L = 10$ kΩ, $A_{VD} = 2$, $f = 10$ kHz	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C		2		MHz
	$R_L = 600$ Ω, $C_L = 100$ pF	25°C		1.5		
Settling time	0.1%	25°C		5		μs
	0.01%	25°C		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10$ kΩ	25°C		40		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10$ kΩ, $C_L = 100$ pF	25°C		60°		
	$R_L = 600$ Ω, $C_L = 100$ pF	25°C		70°		

† Full range is –55°C to 125°C.

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electrical characteristics at $V_{CC\pm} = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TLE2062Y			UNIT
		MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{IC} = 0$, $R_S = 50\ \Omega$		0.9	4	mV
α_{VIO} Input offset voltage long-term drift (see Note 4)			0.04		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current			2		pA
I_{IB} Input bias current			4		pA
V_{ICR} Common-mode input voltage range		-11 to 13	-12 to 16		V
V_{OM+} Maximum positive peak output voltage swing	$R_L = 10\ \text{k}\Omega$	13.2	13.7		V
	$R_L = 600\ \Omega$	12.5	13.2		
V_{OM-} Maximum negative peak output voltage swing	$R_L = 10\ \text{k}\Omega$	-13.2	-13.7		V
	$R_L = 600\ \Omega$	-12.5	-13		
A_{VD} Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$, $R_L = 10\ \text{k}\Omega$	30	230		V/mV
	$V_O = 0$ to $8\ \text{V}$, $R_L = 600\ \Omega$	25	100		
	$V_O = 0$ to $-8\ \text{V}$, $R_L = 600\ \Omega$	3	25		
r_i Input resistance			10^{12}		Ω
c_i Input capacitance			4		pF
z_o Open-loop output impedance	$I_O = 0$		560		Ω
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICR\text{min}}$, $R_S = 50\ \Omega$	72	90		dB
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{CC}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5\ \text{V}$ to $\pm 15\ \text{V}$, $R_S = 50\ \Omega$	75	93		dB
I_{CC} Supply current	$V_O = 0$, No load		625	690	μA

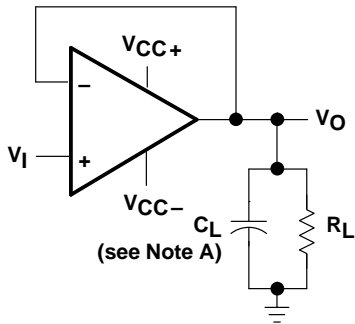
NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

operating characteristics at $V_{CC\pm} = \pm 15\ \text{V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TLE2062Y			UNIT
		MIN	TYP	MAX	
SR Slew rate at unity gain	$R_L = 10\ \text{k}\Omega$, $C_L = 100\ \text{pF}$	2.6	3.4	4	V/ μs
V_n Equivalent input noise voltage (see Figure 2)	$f = 10\ \text{Hz}$, $R_S = 20\ \Omega$		70		nV/ $\sqrt{\text{Hz}}$
	$f = 1\ \text{kHz}$, $R_S = 20\ \Omega$		40		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\ \text{Hz}$ to $10\ \text{Hz}$		1.1		μV
I_n Equivalent input noise current	$f = 1\ \text{Hz}$		1.1		fA/ $\sqrt{\text{Hz}}$
THD Total harmonic distortion	$V_{O(PP)} = 2\ \text{V}$, $R_L = 10\ \text{k}\Omega$, $A_{VD} = 2$, $f = 10\ \text{kHz}$		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10\ \text{k}\Omega$, $C_L = 100\ \text{pF}$		2		MHz
	$R_L = 600\ \Omega$, $C_L = 100\ \text{pF}$		1.5		
Settling time	0.1%		5		μs
	0.01%		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10\ \text{k}\Omega$		40		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10\ \text{k}\Omega$, $C_L = 100\ \text{pF}$		60°		
	$R_L = 600\ \Omega$, $C_L = 100\ \text{pF}$		70°		



PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes fixture capacitance.

Figure 1. Slew-Rate Test Circuit

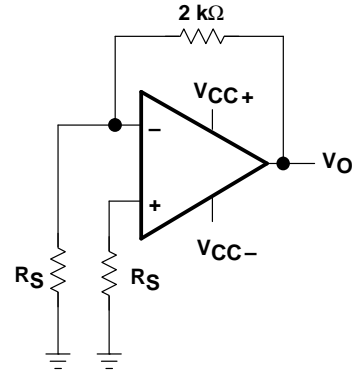
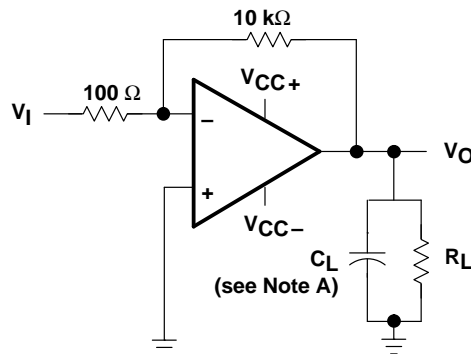


Figure 2. Noise-Voltage Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 3. Unity-Gain Bandwidth and Phase-Margin Test Circuit

typical values

Typical values presented in this data sheet represent the median (50% point) of device parametric performance.

input bias offset current

At the picoamp bias current level typical of the TLE2062, TLE2062A, and TLE2062B, accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test socket leakages can easily exceed the actual device bias currents. To accurately measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied but with no device in the socket. The device is then inserted into the socket and a second test that measures both the socket leakage and the device input bias current is performed. The two measurements are then subtracted algebraically to determine the bias current of the device.

TYPICAL CHARACTERISTICS

Table of Graphs

		FIGURE
V_{IO}	Input offset voltage	Distribution 4
I_{IB}	Input bias current	vs Common-mode voltage 5
		vs Free-air temperature 6
I_{IO}	Input offset current	vs Free-air temperature 6
V_{ICR}	Common-mode input voltage range	vs Free-air temperature 7
V_{OM}	Maximum peak output voltage swing	vs Output current 8,9
		vs Supply voltage 10,11,12
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency 13,14
A_{VD}	Large-signal differential voltage amplification	vs Frequency 15
		vs Free-air temperature 16
I_{OS}	Short-circuit output current	vs Time 17
		vs Free-air temperature 18
z_o	Output impedance	vs Frequency 19
CMRR	Common-mode rejection ratio	vs Frequency 20
I_{CC}	Supply current	vs Supply voltage 21
		vs Free-air temperature 22
	Pulse response	Small signal 23,24 Large signal 25,26
	Noise voltage (referred to input)	0.1 to 10 Hz 27
V_n	Equivalent input noise voltage	vs Frequency 28
THD	Total harmonic distortion	vs Frequency 29,30
B_1	Unity-gain bandwidth	vs Supply voltage 31
		vs Free-air temperature 32
ϕ_m	Phase margin	vs Supply voltage 33
		vs Load capacitance 34
		vs Free-air temperature 35
	Phase shift	vs Frequency 15

TYPICAL CHARACTERISTICS†

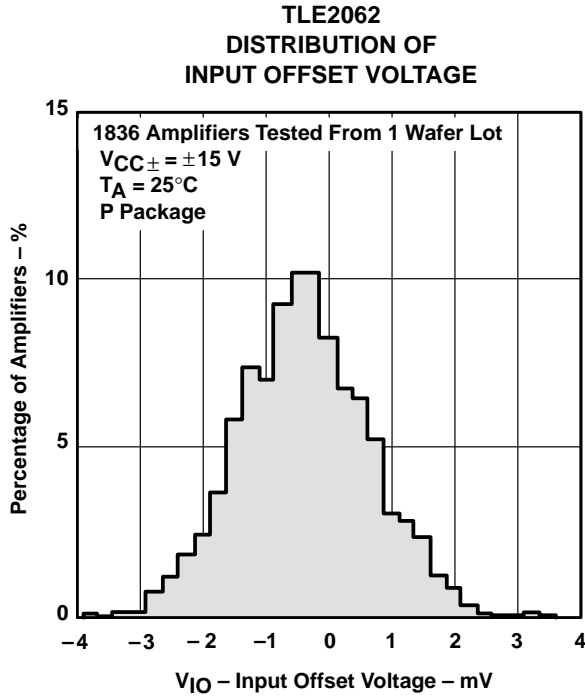


Figure 4

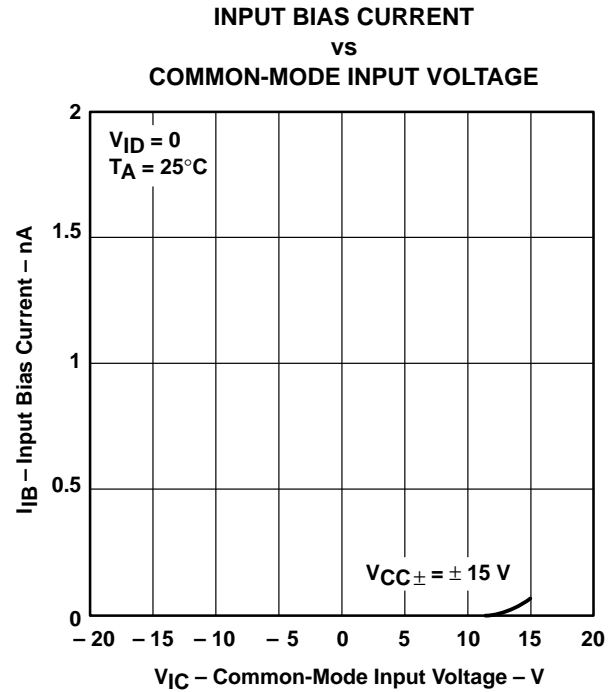


Figure 5

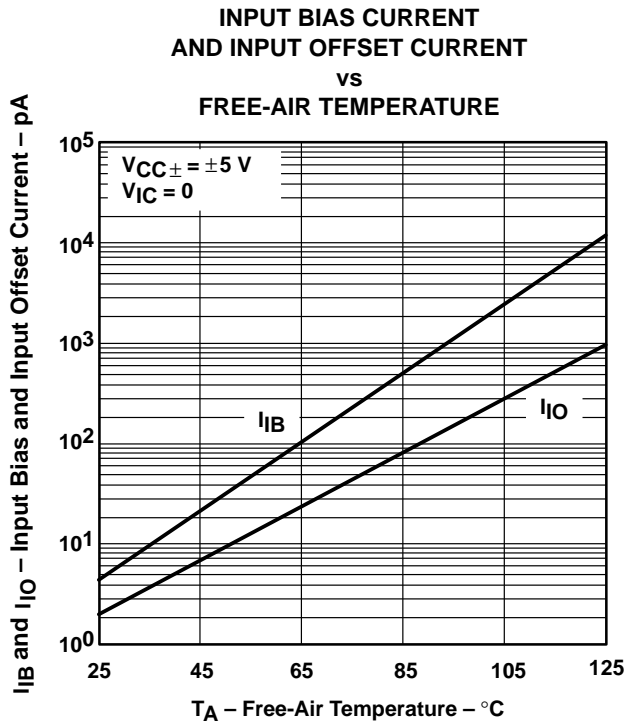


Figure 6

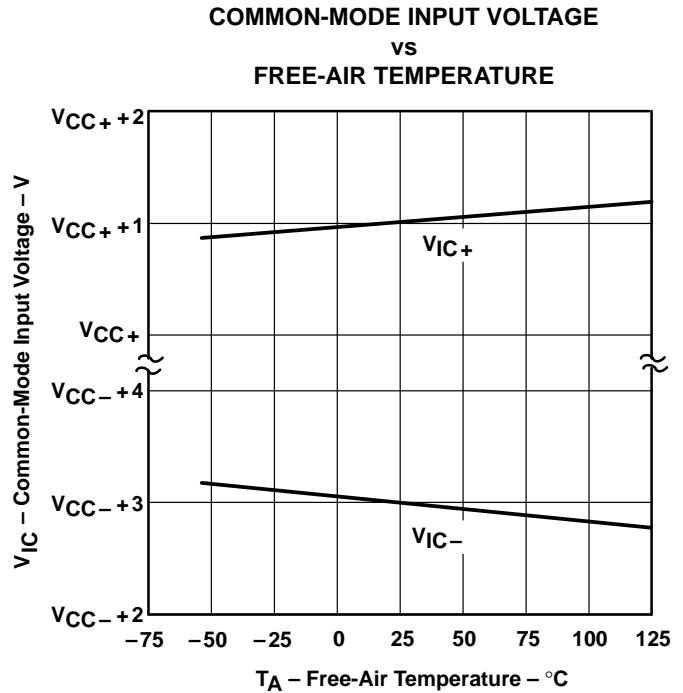


Figure 7

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

MAXIMUM POSITIVE PEAK
 OUTPUT VOLTAGE
 vs
 OUTPUT CURRENT

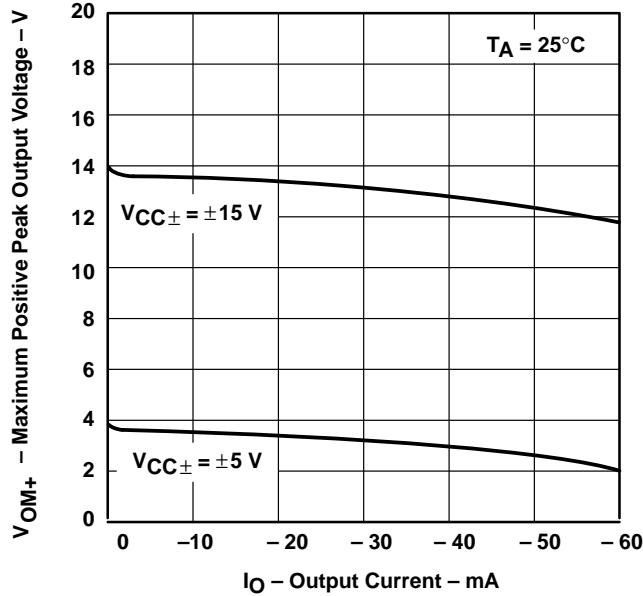


Figure 8

MAXIMUM NEGATIVE PEAK
 OUTPUT VOLTAGE
 vs
 OUTPUT CURRENT

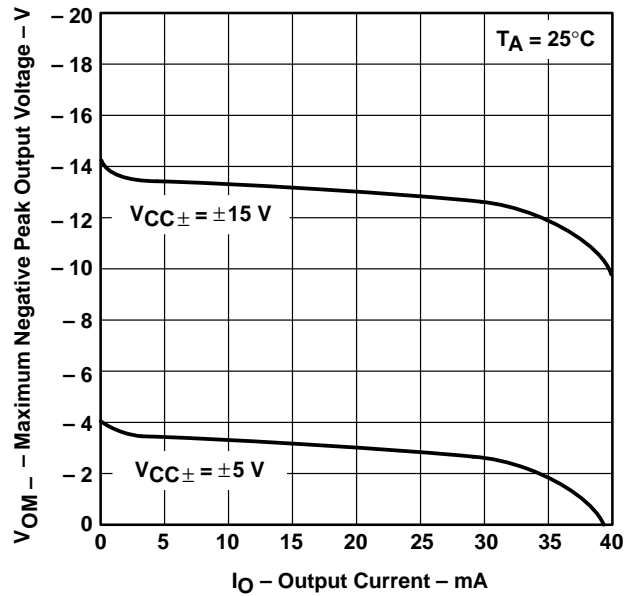


Figure 9

MAXIMUM PEAK OUTPUT VOLTAGE
 vs
 SUPPLY VOLTAGE

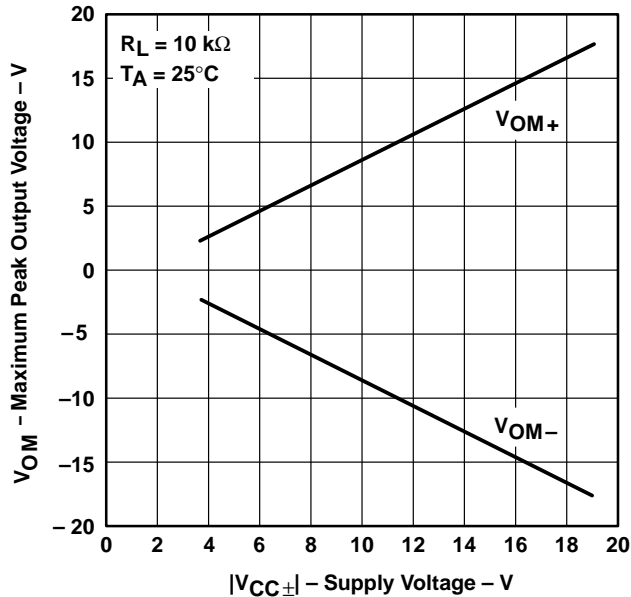


Figure 10

MAXIMUM PEAK OUTPUT VOLTAGE
 vs
 SUPPLY VOLTAGE

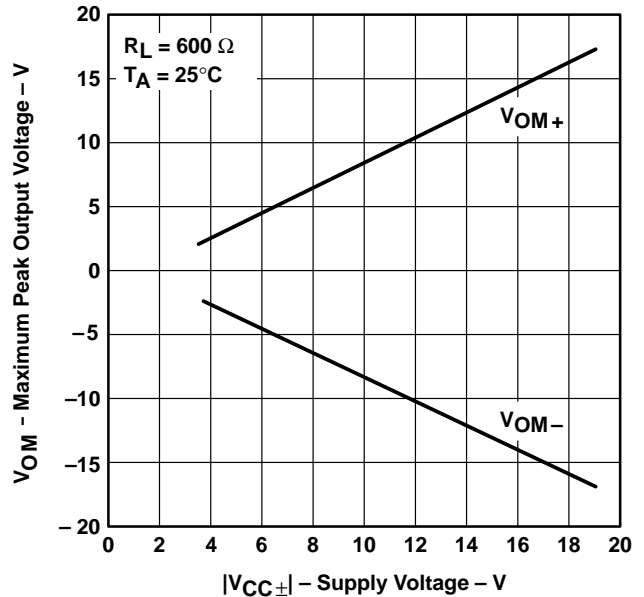


Figure 11

TYPICAL CHARACTERISTICS

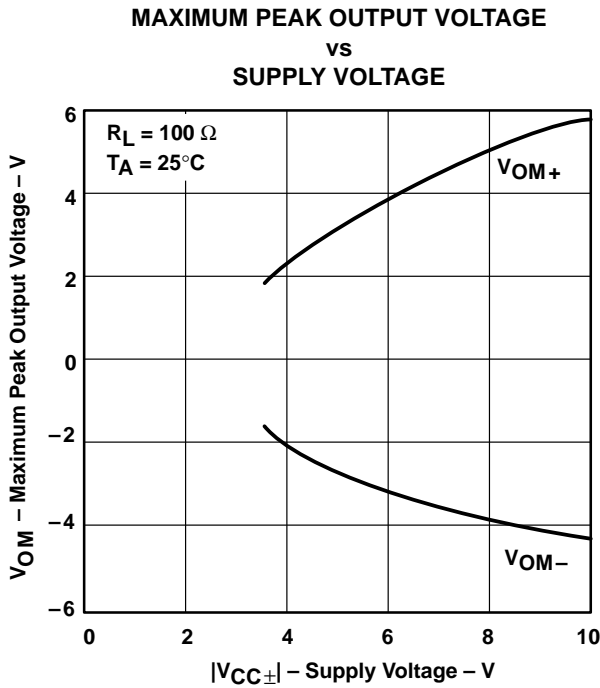


Figure 12

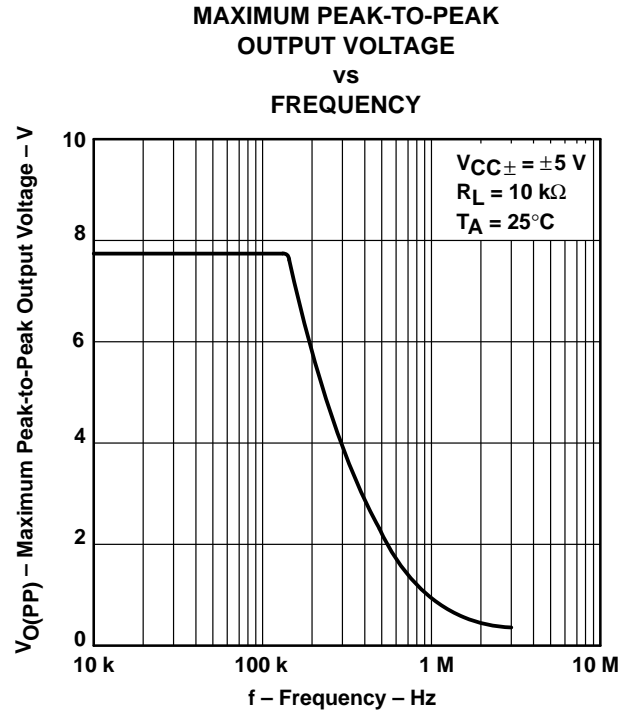


Figure 13

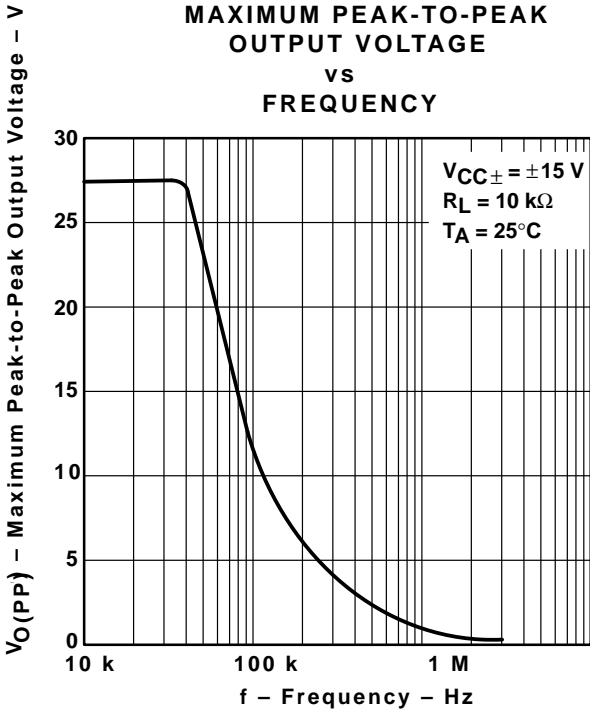


Figure 14

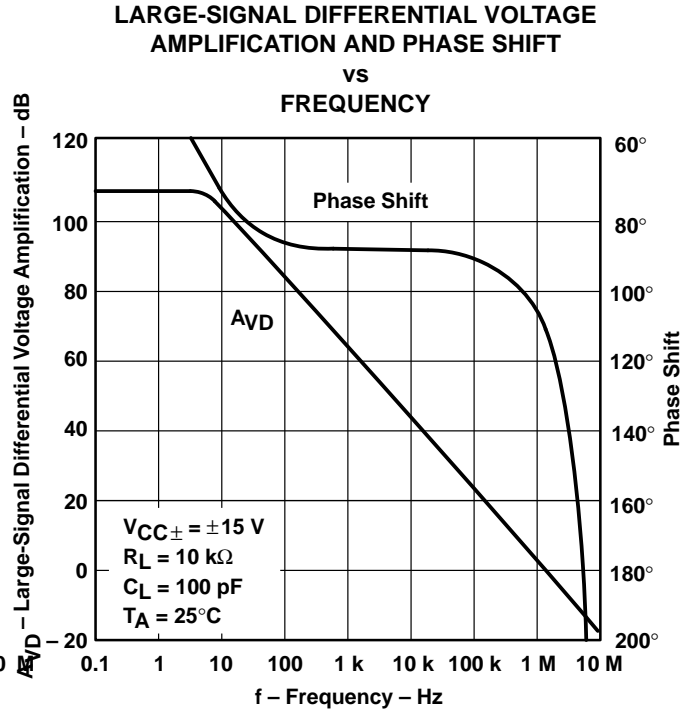


Figure 15

TYPICAL CHARACTERISTICS

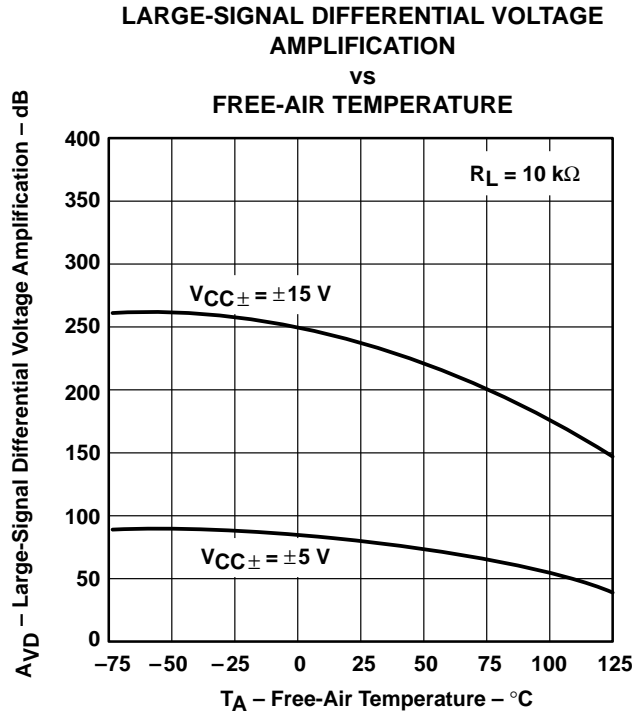


Figure 16

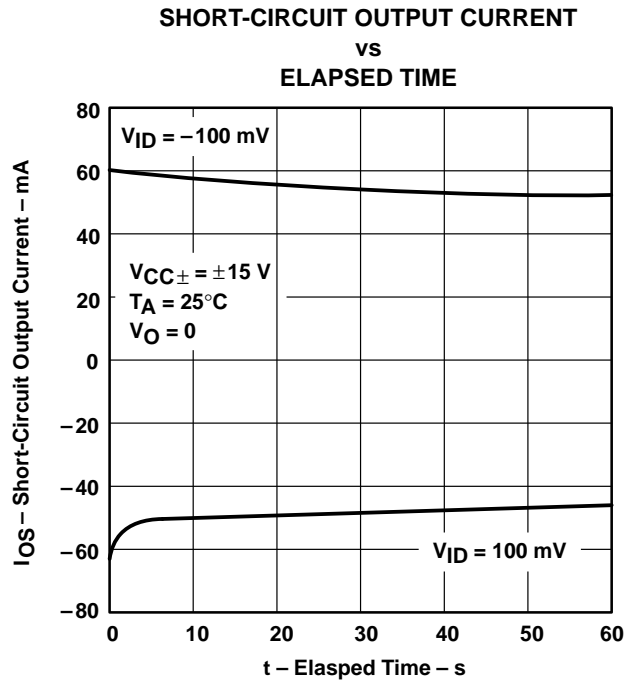


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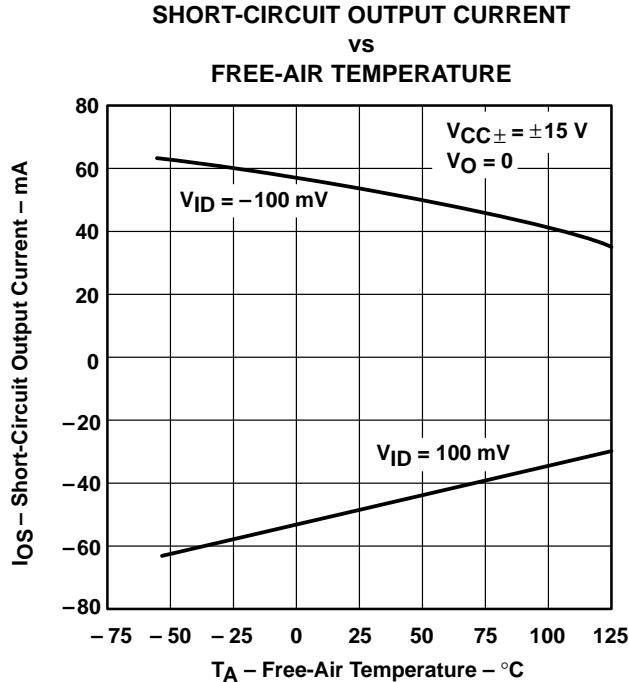


Figure 18

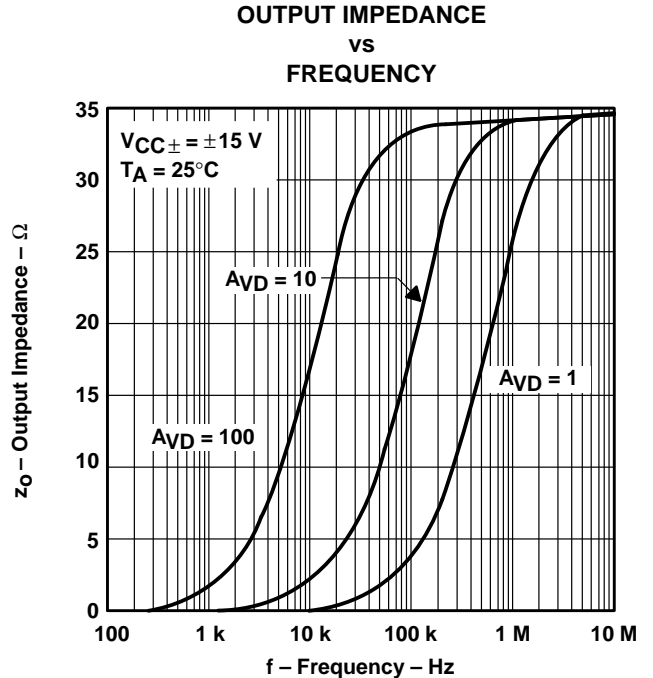


Figure 19

TYPICAL CHARACTERISTICS†

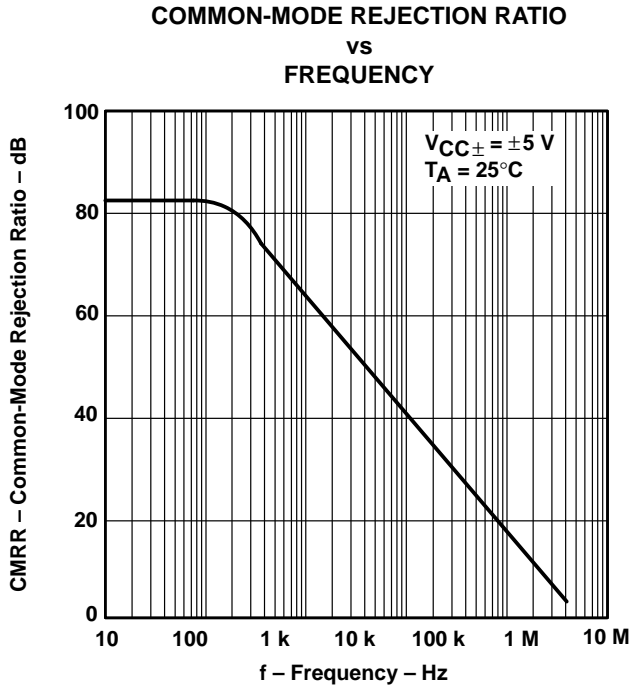


Figure 20

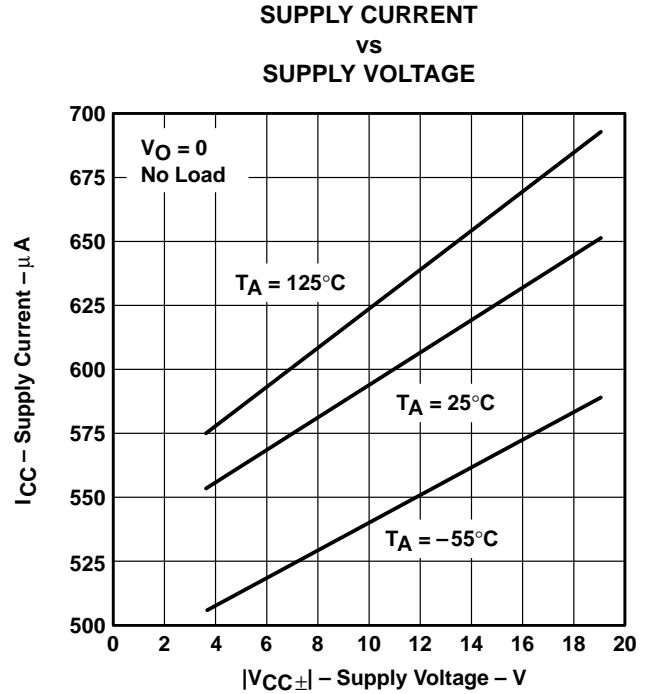


Figure 21

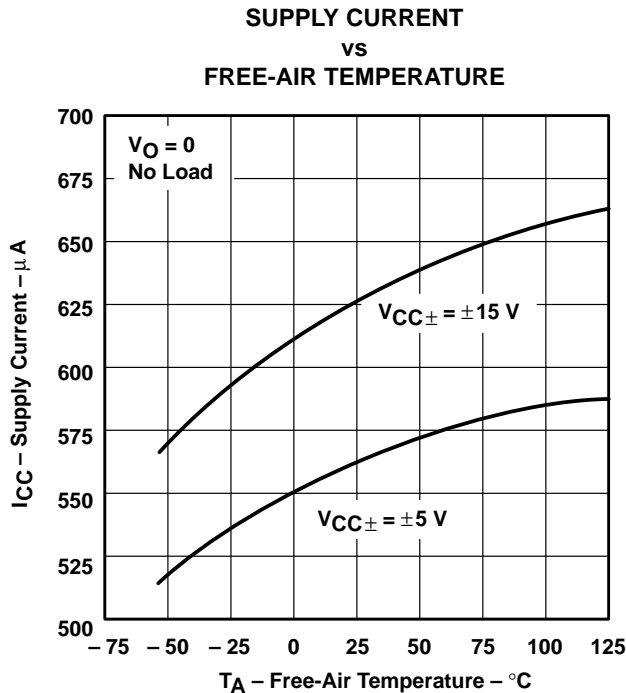


Figure 22

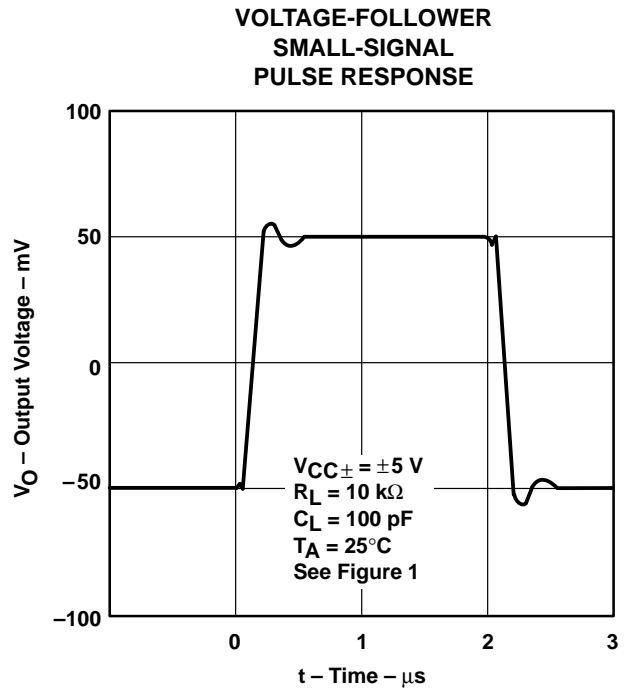


Figure 23

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

VOLTAGE-FOLLOWER
 SMALL-SIGNAL
 PULSE RESPONSE

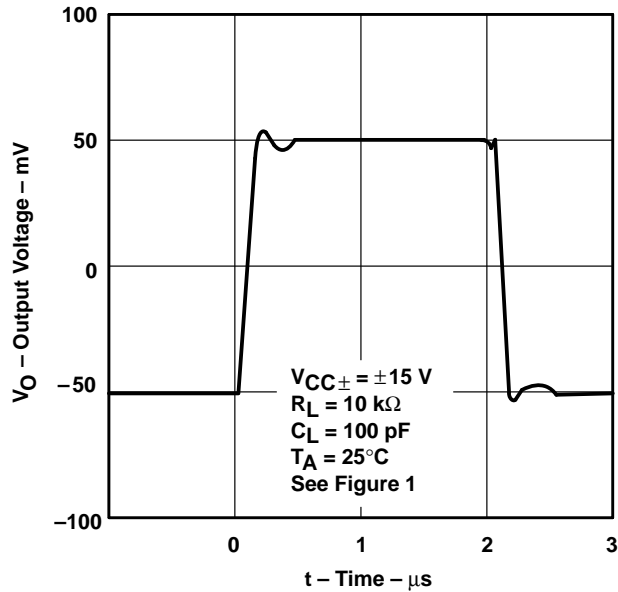


Figure 24

VOLTAGE-FOLLOWER
 LARGE-SIGNAL
 PULSE RESPONSE

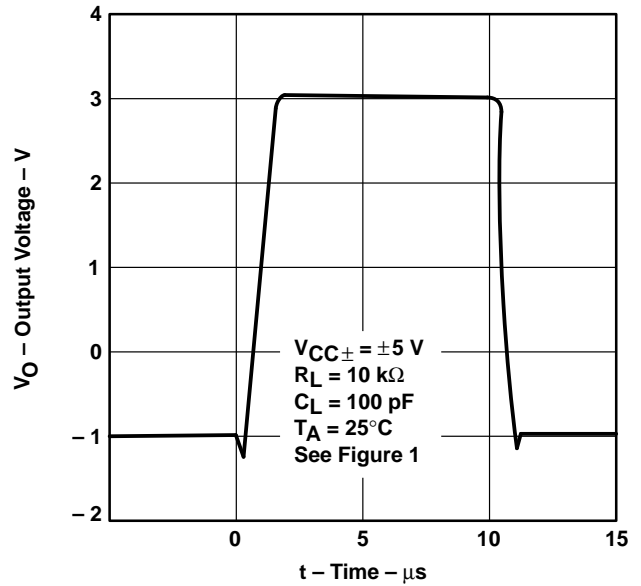


Figure 25

VOLTAGE-FOLLOWER
 LARGE-SIGNAL
 PULSE RESPONSE

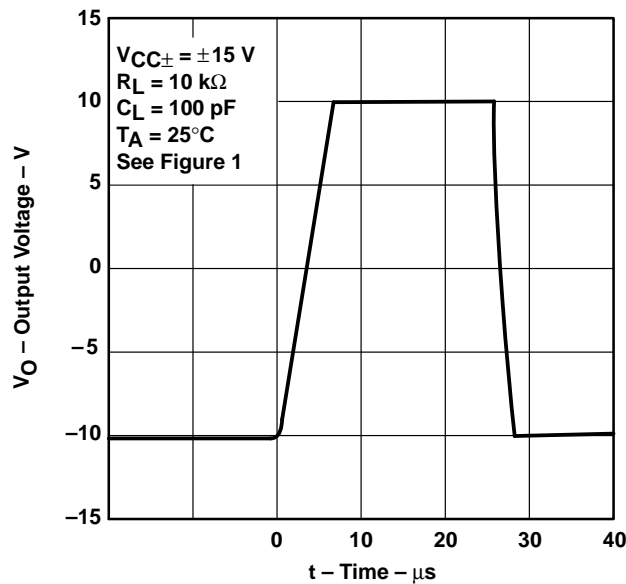


Figure 26

NOISE VOLTAGE
 (REFERRED TO INPUT)
 0.1 TO 10 Hz

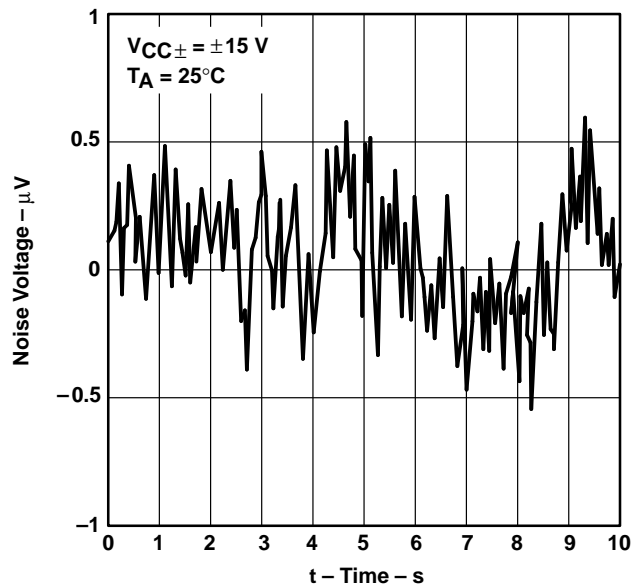


Figure 27

TYPICAL CHARACTERISTICS

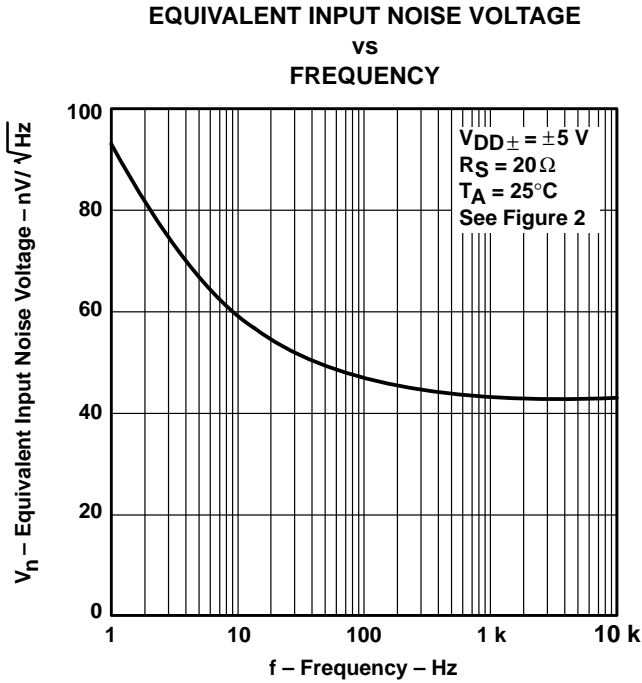


Figure 28

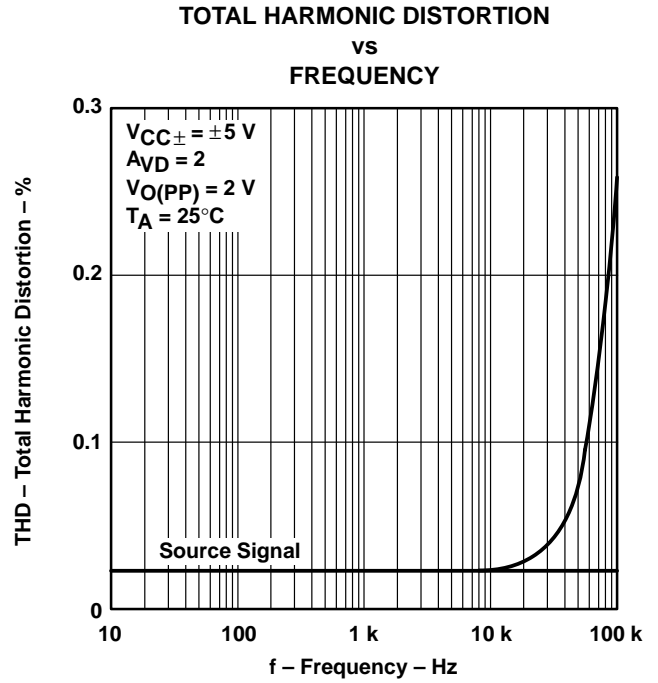


Figure 29

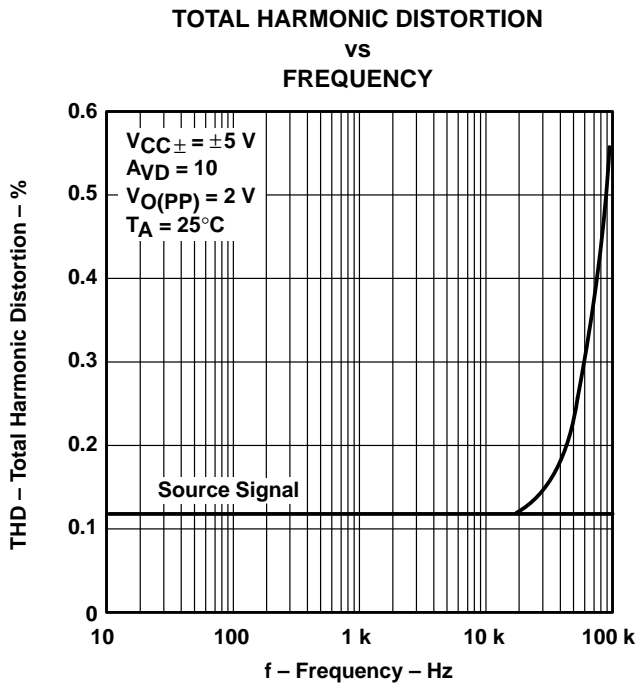


Figure 30

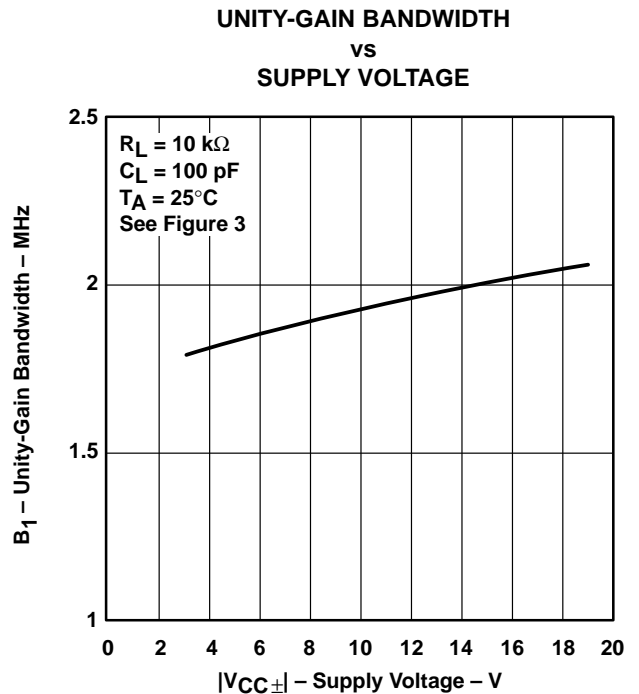


Figure 31

TYPICAL CHARACTERISTICS†

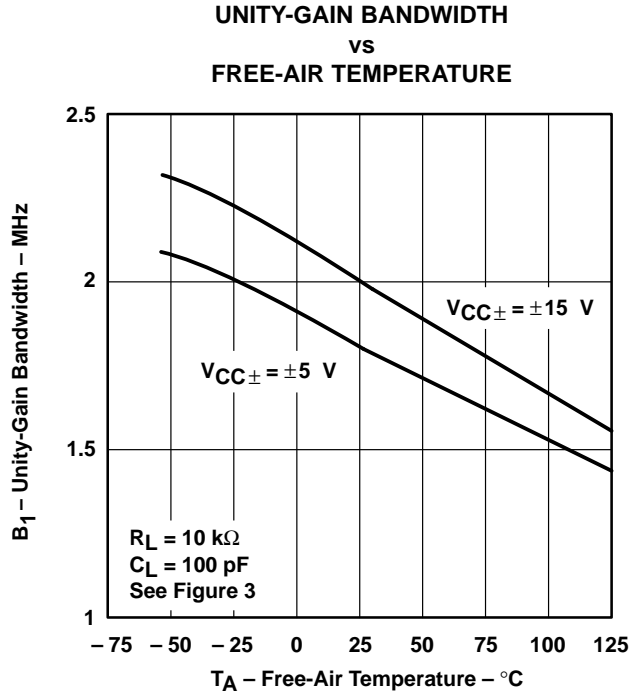


Figure 32

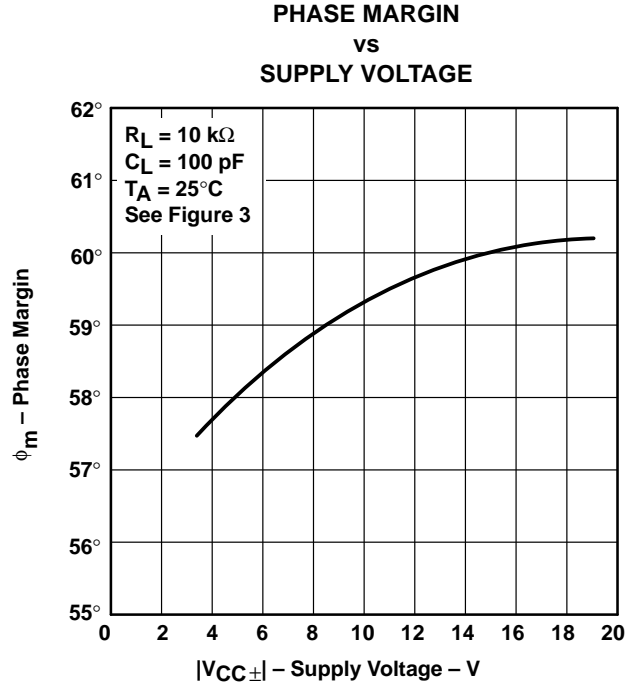


Figure 33

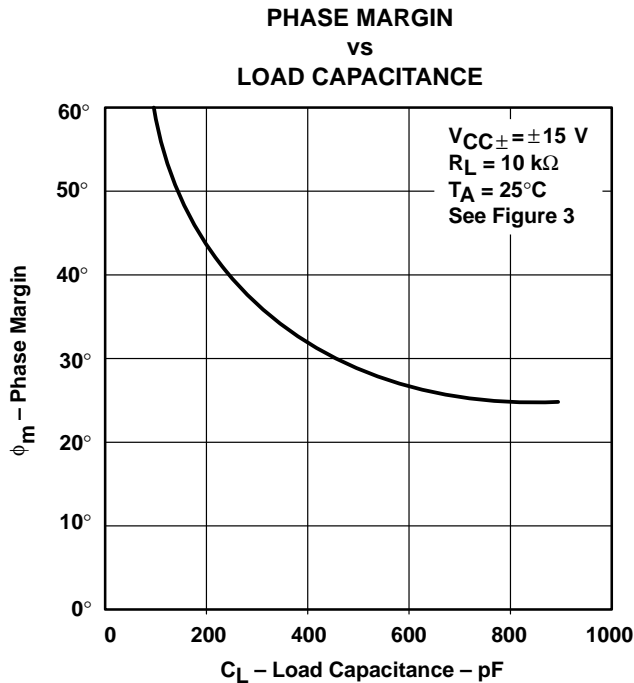


Figure 34

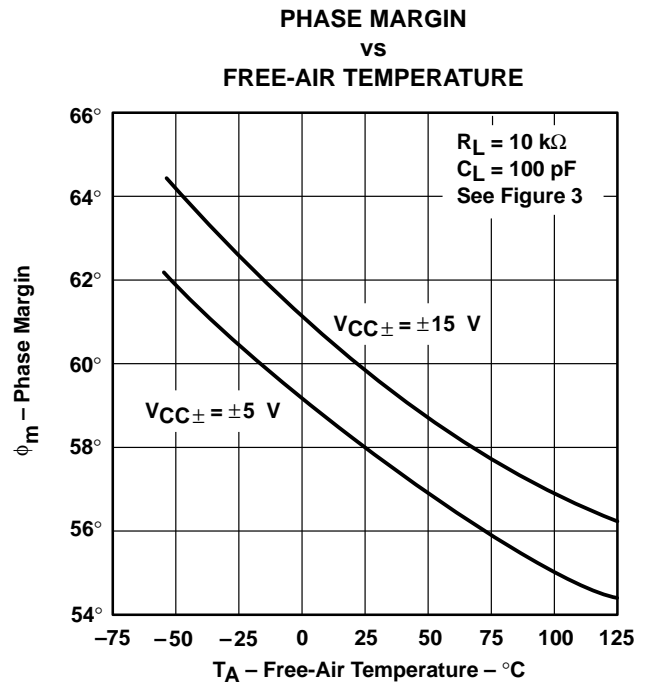


Figure 35

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

APPLICATION INFORMATION

input characteristics

The TLE2062, TLE2062A, and TLE2062B are specified with a minimum and a maximum input voltage that if exceeded at either input could cause the device to malfunction.

Because of the extremely high input impedance and resulting low bias current requirements, the TLE2062, TLE2062A, and TLE2062B are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause degradation in system performance. It is a good practice to include guard rings around inputs (see Figure 38). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input.

The inputs of any unused amplifiers should be tied to ground to avoid possible oscillation.

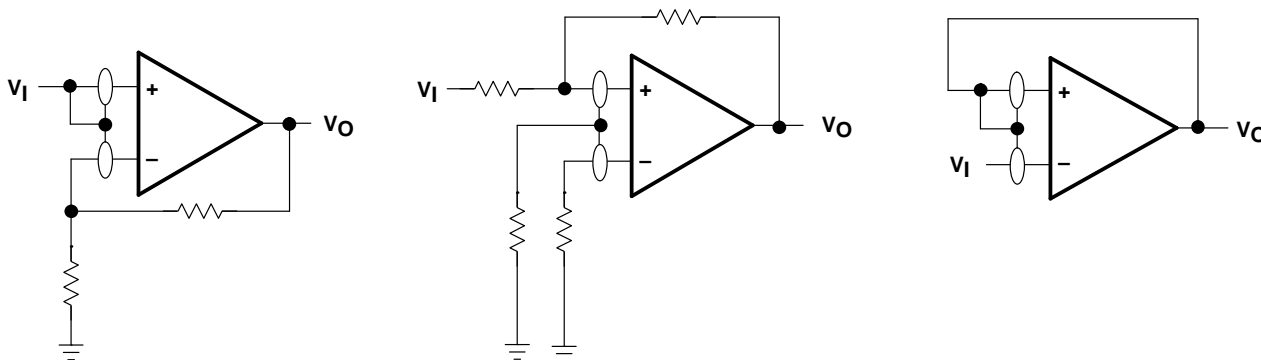


Figure 36. Use of Guard Rings

TLE2062, TLE2062A, TLE2062B, TLE2062Y EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE μPOWER DUAL OPERATIONAL AMPLIFIERS

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APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using *PSpice™ Parts™* model generation software. The Boyle macromodel (see Note 5) and subcircuit in Figure 37 were generated using the TLE2062 typical electrical and operating characteristics at 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 5: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

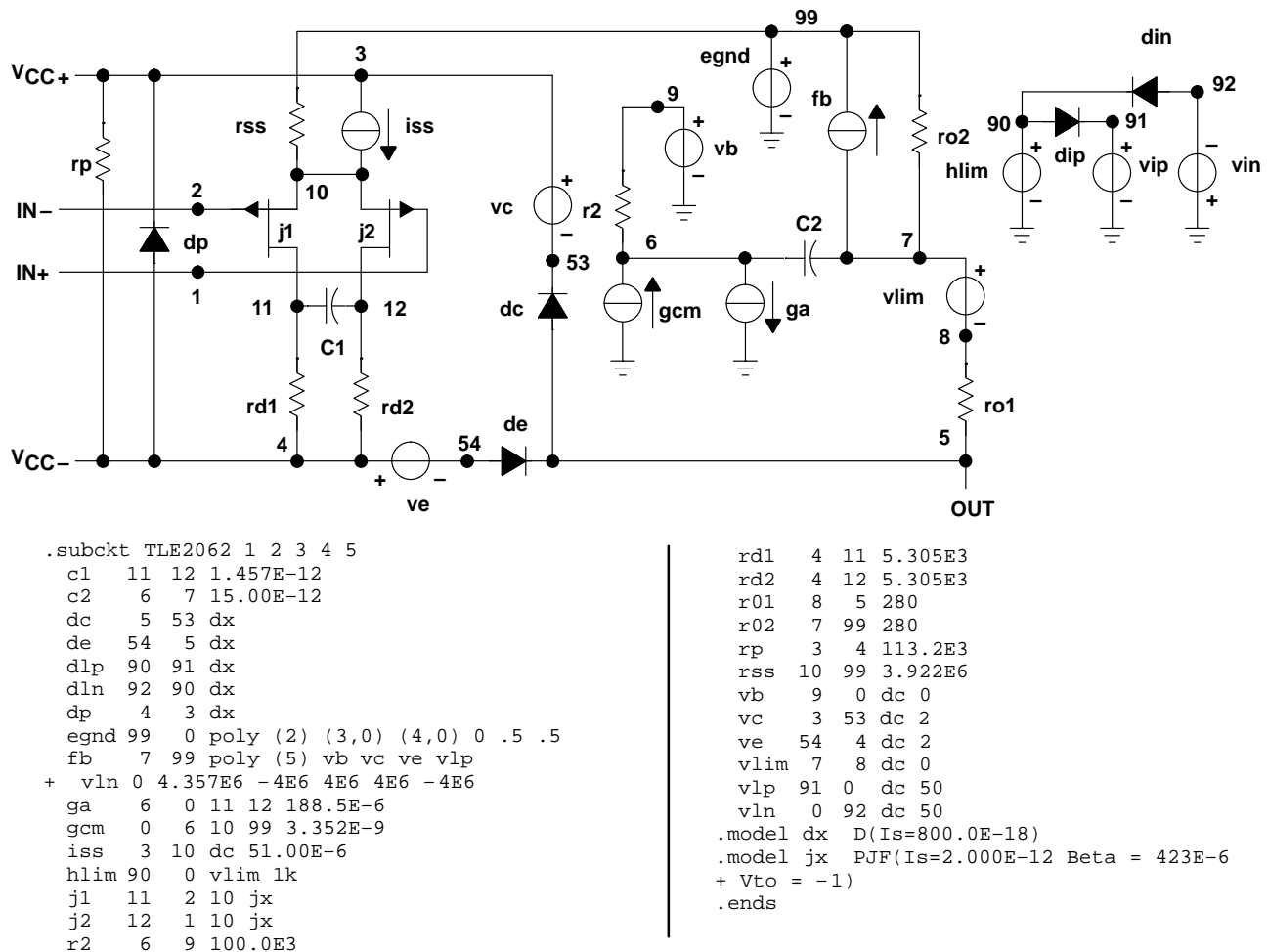


Figure 37. Boyle Macromodel and Subcircuit

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